NUP2114 Se ie , SNUP2114

ESD P o ec ion Diode

Low Capacitance ESD Protection for High Speed Data

The NUP2114 surge protection is designed to protect high speed data lines from ESD. Ultra-low capacitance and high level of ESD protection makes this device well suited for use in USB 2.0 applications.

Features

- Low Capacitance 0.8 pF
- Low Clamping Voltage
- Stand Off Voltage: 5 V
- Low Leakage
- ESD Rating of Class 3B (Exceeding 8 kV) per Human Body model and Class C (Exceeding 400 V) per Machine Model
- Protection for the Following IEC Standards: IEC 61000–4–2 Level 4 ESD Protection
- UL Flammability Rating of 94 V-0
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- High Speed Communication Line Protection
- USB 2.0 High Speed Data Line and Power Line Protection
- Monitors and Flat Panel Displays
- MP3
- Gigabit Ethernet
- Notebook Computers
- Digital Video Interface (DVI) and HDMI

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Operating Junction Temperature Range	T_J	-40 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Lead Solder Temperature – Maximum (10 Seconds)	TL	260	°C
Human Body Model (HBM) Machine Model (MM) IEC 61000-4-2 Contact IEC61000-4-2 Air	ESD	16000 400 13000 15000	٧

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

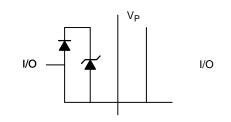
See Application Note AND8308/D for further description of survivability specs.



www.onsemi.com



SOT-553 CASE 463B



MARKING DIAGRAMS

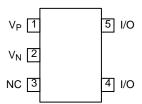


P2, P2M = Specific Device Code

M = Date Code

= Pb-Free Package

PIN CONNECTIONS



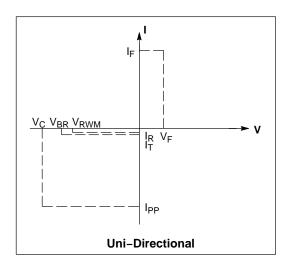
NUP2114 Series, SNUP2114

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ I _{PP}
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V_{BR}	Breakdown Voltage @ I _T
Ι _Τ	Test Current
IF	Forward Current
V _F	Forward Voltage @ I _F
P _{pk}	Peak Power Dissipation
С	Max. Capacitance @ $V_R = 0$ and $f = 1.0$ MHz

^{*}See Application Note AND8308/D for detailed explanations of datasheet parameters.



NUP2114 Series, SNUP2114

IEC 61000-4-2 Spec.

	Test Volt-	First Peak Current	Current at
Level	age (kV)	(A)	

NUP2114 Series, SNUP2114

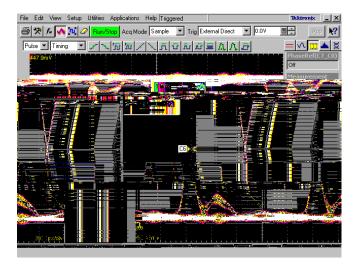


Figure 6. 500 MHz Data Pattern

ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NUP2114UPXV5T1G	P2	SOT-553 (Pb-Free)	4,000 / Tape & Reel
NUP2114UCMR6T1G	P2M	TSOP-6 (Pb-Free)	3,000 / Tape & Reel
SNUP2114UCMR6T1G*	P2M	TSOP-6 (Pb-Free)	3,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



TSOP-6 3.00x1.50x0.90, 0.95P CASE 318G ISSUE W

DATE 26 FEB 2024

NOTES: 1. DIMENSIONING AND TOLERAN

TSOP-6 3.00x1.50x0.90, 0.95P

CASE 318G ISSUE W

DATE 26 FEB 2024

GENERIC MARKING DIAGRAM*



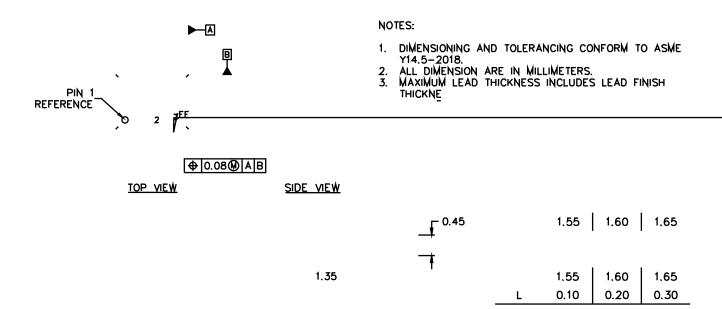


XXX = Specific Device Code A = Assembly Location Y = Year

W = Work Week

■ = Pb-Free Package

STYLE 1: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 2: PIN 1. EMITTER 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. BASE 2 6. COLLECTOR 2	STYLE 3: PIN 1. ENABLE 2. N/C 3. R BOOST 4. Vz 5. V in 6. V out	STYLE 4: PIN 1. N/C 2. V in 3. NOT USED 4. GROUND 5. ENABLE 6. LOAD	STYLE 5: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 6: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR
STYLE 7: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. N/C 5. COLLECTOR 6. EMITTER	STYLE 8: PIN 1. Vbus 2. D(in) 3. D(in)+ 4. D(out)+ 5. D(out) 6. GND	STYLE 9: PIN 1. LOW VOLTAGE GATE 2. DRAIN 3. SOURCE 4. DRAIN 5. DRAIN 6. HIGH VOLTAGE GATE	STYLE 10: PIN 1. D(OUT)+ 2. GND 3. D(OUT)- 4. D(IN)- 5. VBUS 6. D(IN)+	STYLE 11: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1/GATE 2	STYLE 12: PIN 1. I/O 2. GROUND 3. I/O 4. I/O 5. VCC 6. I/O



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